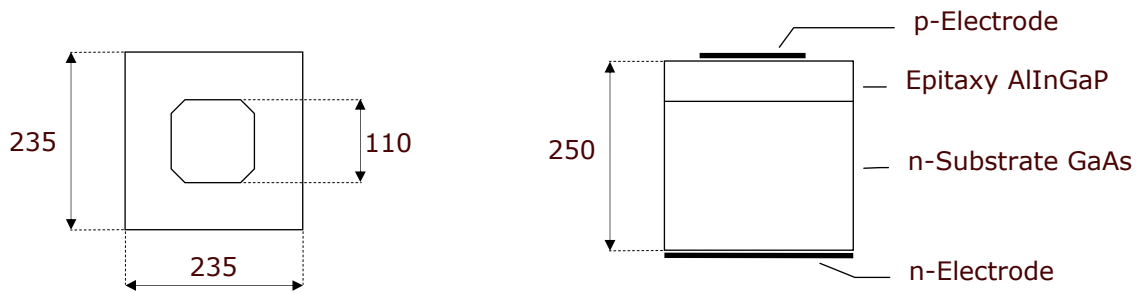


**RED**

**Item No.: 193252**

1. This specification applies to AlInGaP / GaAs LED Chips
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

p-side (anode)	Au alloy or Al
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	$V_F$	$I_F = 20 \text{ mA}$		2,10	2,40	V
Reverse current	$I_R$	$V_R = 5 \text{ V}$			10	$\mu\text{A}$
Luminous intensity *	$I_V$	$I_F = 10 \text{ mA}$		10,0		mcd
dom. wavelength	$\lambda_D$	$I_F = 20 \text{ mA}$		632		nm

\* On request, wafers will be delivered according to luminous intensity classes  
 Brightness measurement at OSA on gold plate

5. Packing
  - 1) wire bond side on top
  - 2) back contact on top

6. Labeling

Type	Lot No.	$I_V$ typ min max	Quantity